

Effects of Annular Beam Properties on Gap Coupling in High-Frequency Microwave Devices



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Abstract

- This work studies the interaction of an **annular** electron beam with a cavity gap.
- We provide a **parametric analysis** of beam-cavity interaction for large signals of linear beam device.
- We compare the **gap coupling factor** of annular and solid beams for the same beam current.
- We observe the effect of space charge on the **electron trajectories** and their **kinetic energy** which leads to lower conversion efficiency.

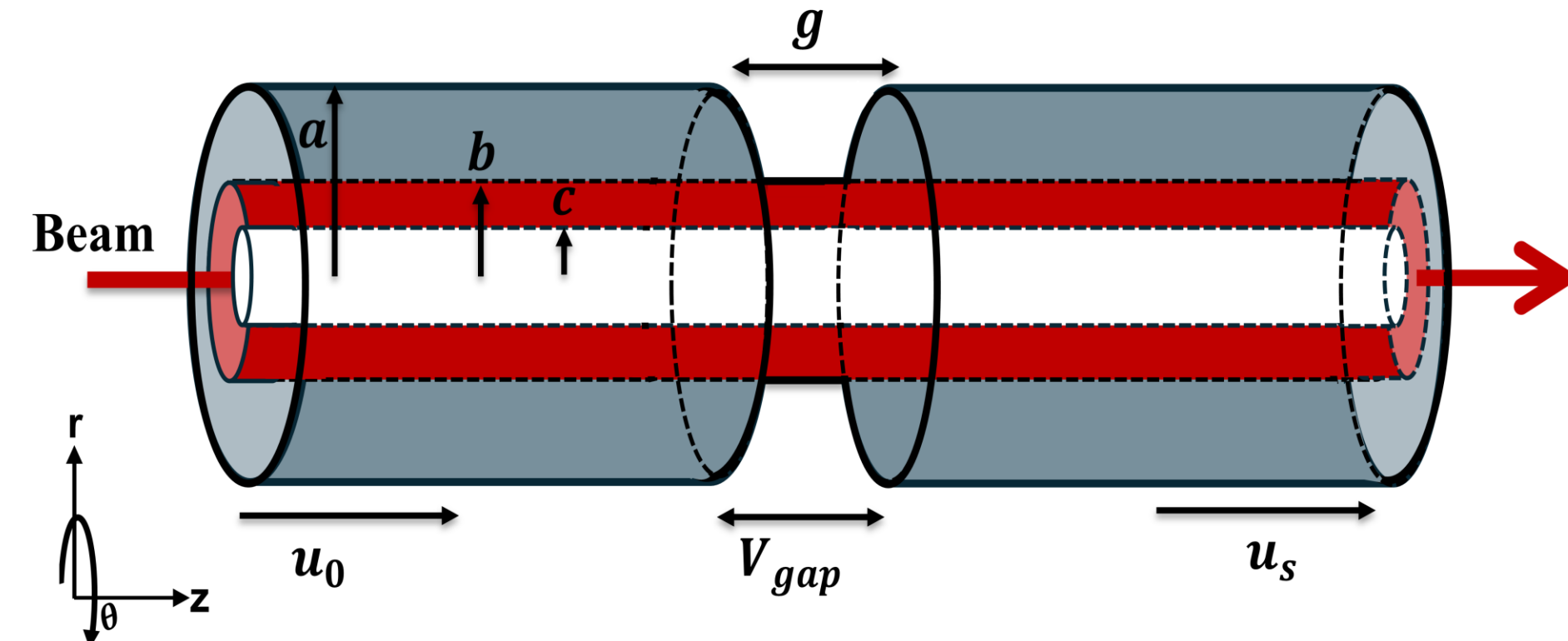


Fig. 1. Interaction gap of an annular linear beam device [1]

Methodology

Disk Model

Space charge Field, E_{sc} =

$$\begin{cases} \frac{4\rho_c}{\epsilon_0} \sum_{m=1}^{\infty} \frac{1}{\mu_m} \frac{[bJ_1(\mu_m b) - cJ_1(\mu_m c)]^2 e^{-\mu_m |z-z_0|}}{(b^2 - c^2)^3 [J_1(\mu_m a)]^2} \sinh\left(\frac{\mu_m L}{2}\right) & \text{for } |z| > \frac{L}{2} \\ \frac{4\rho_c}{\epsilon_0} \sum_{m=1}^{\infty} \frac{1}{\mu_m} \frac{[bJ_1(\mu_m b) - cJ_1(\mu_m c)]^2 e^{-\frac{\mu_m L}{2}}}{(b^2 - c^2)^3 [J_1(\mu_m a)]^2} \sinh \mu_m (z - z_0) & \text{for } |z| < \frac{L}{2} \end{cases}$$

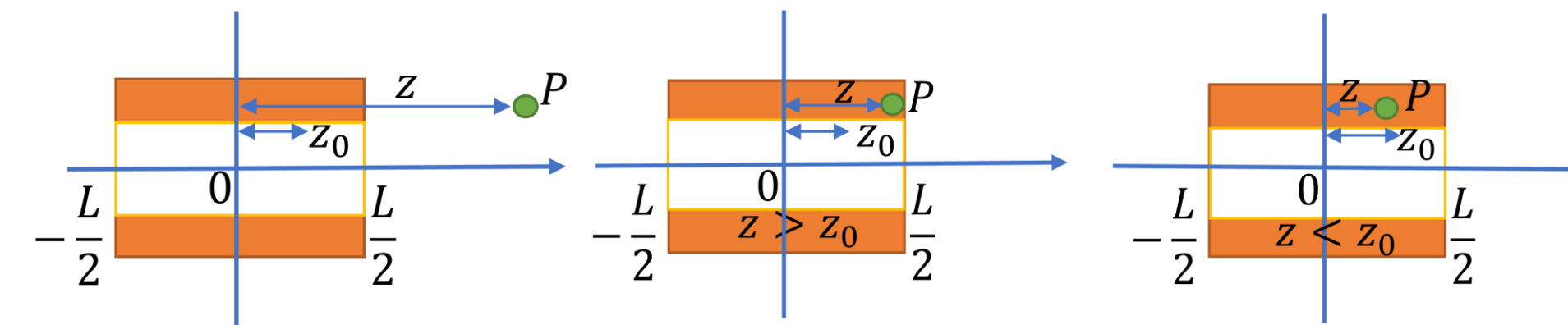


Fig. 2. Space charge potential for outside ($z > z_0$) and inside ($z < z_0$) the gap.

Equation of motion,

$$\frac{du_{si}}{dt} = \eta_e \left(1 - \frac{u_{si}^2}{c^2}\right)^{3/2} [E_z(z_i) \cos(\omega t) + \sum_{j=1}^{N_D} \frac{Q}{e} E_{sc}(z_i - z_j)]$$

DC beam power of the disk model,

$$P_{DC} = KE_0 \times f$$

RF power transferred to the gap from the change in KE

$$P_{RF} = (KE_0 - KE_{max}) \times f$$

Efficiency of the linear beam device,

$$\eta = \frac{P_{RF}}{P_{DC}} = \frac{(KE_0 - KE_{max}) \times f}{KE_0 \times f}$$

Methodology

TABLE I. Parameters for Calculation [2]

Anode Voltage, V_a	25kV
Load Impedance, R_L	26k Ω
Frequency, f	1.3GHz
Number of Disks, N_D	50
Disk length, L	0.8mm
Output gap Length, g	11mm

TABLE II. List of Symbols

a	Tunnel radius
b	Outer Beam radius
c	Inner Beam radius
ρ_c	Space charge density
ω	Angular frequency
I_b	Beam current
I_{RF}	RF current
Q	Disk Charge
η_e	Charge/mass ratio

Analytical Model

- Wave number, $\beta = \frac{\omega}{u}$
- Small Signal **Gap Coupling Coefficient**,

$$M = \frac{2[bI_1(\beta(u)b) - cI_1(\beta c)] \sin\left(\frac{\beta(u)g}{2}\right)}{\beta(u)(b^2 - c^2)I_0(\beta(u)a) \left(\frac{\beta(u)g}{2}\right)}$$

- Large Signal **Gap Coupling Coefficient**,

$$M = \frac{2[bI_1\left(\beta\left(\frac{u_0 + u_s}{2}\right)b\right) - cI_1\left(\beta\left(\frac{u_0 + u_s}{2}\right)c\right)] \sin\left(\frac{\beta\left(\frac{u_0 + u_s}{2}\right)g}{2}\right)}{\beta\left(\frac{u_0 + u_s}{2}\right)(b^2 - c^2)I_0\left(\beta\left(\frac{u_0 + u_s}{2}\right)a\right) \frac{\beta\left(\frac{u_0 + u_s}{2}\right)g}{2}}$$

- RF Output Power, $P_{RF} = \frac{1}{2} M^2 I_{RF}^2 R_L$ [3]

- Electronic Efficiency, $\eta = \frac{P_{out}}{I_b V_a}$

Disk Model

- Axial component of **Electric Field**,

$$E_z(z) = \frac{V_{gap}}{2\pi} \int_{-\infty}^{\infty} \frac{2[bI_1(\beta b) - cI_1(\beta c)] \sin\left(\frac{\beta g}{2}\right)}{\beta(b^2 - c^2)I_0(\beta a) \left(\frac{\beta g}{2}\right)} e^{-j\beta z} d\beta$$

- Gap Voltage, $V_{gap} = I_{RF} M \left(\frac{u_0 + u_s}{2}\right) R_L$

- Kinetic Energy,

$$KE_k = \frac{Q}{\eta_e} c^2 \sum_{j=1}^{N_D} \left(1 - \sqrt{1 - \frac{u_{skj}^2}{c^2}} - 1\right)$$

Results

Normalized Gap Coupling Factor

- Length scale $L = 1/\beta \left(\frac{u_0 + u_s}{2}\right)$, normalized tunnel, outer & inner beam radius, and gap length are $\bar{a} = \frac{a}{L}$, $\bar{b} = \frac{b}{L}$, $\bar{c} = \frac{c}{L}$, $\bar{g} = \frac{g}{L}$. Normalized M :

$$M = \frac{2}{(\bar{b}^2 - \bar{c}^2)} \frac{[\bar{b}I_1(\bar{b}) - \bar{c}I_1(\bar{c})] \sin\left(\frac{\bar{g}}{2}\right)}{I_0(\bar{a}) \left(\frac{\bar{g}}{2}\right)}$$
- Increase of normalized \bar{a} and \bar{g} lowers M for the annular beam, which is similar to solid beam [2]
- Increase of normalized \bar{b} and \bar{c} increases M .

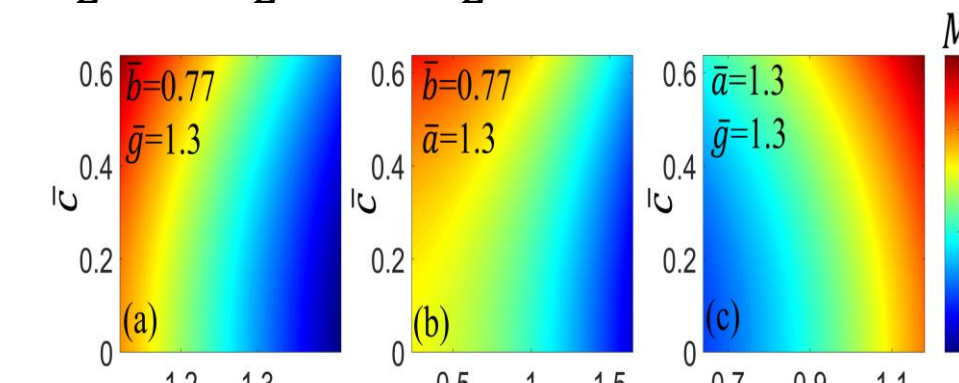


Fig. 5. Comparison of M as a function of (a) \bar{a} and \bar{b} , (b) \bar{c} and \bar{b} , (c) \bar{c} and \bar{b}

B. Constant Outer Beam Radius and Beam Current

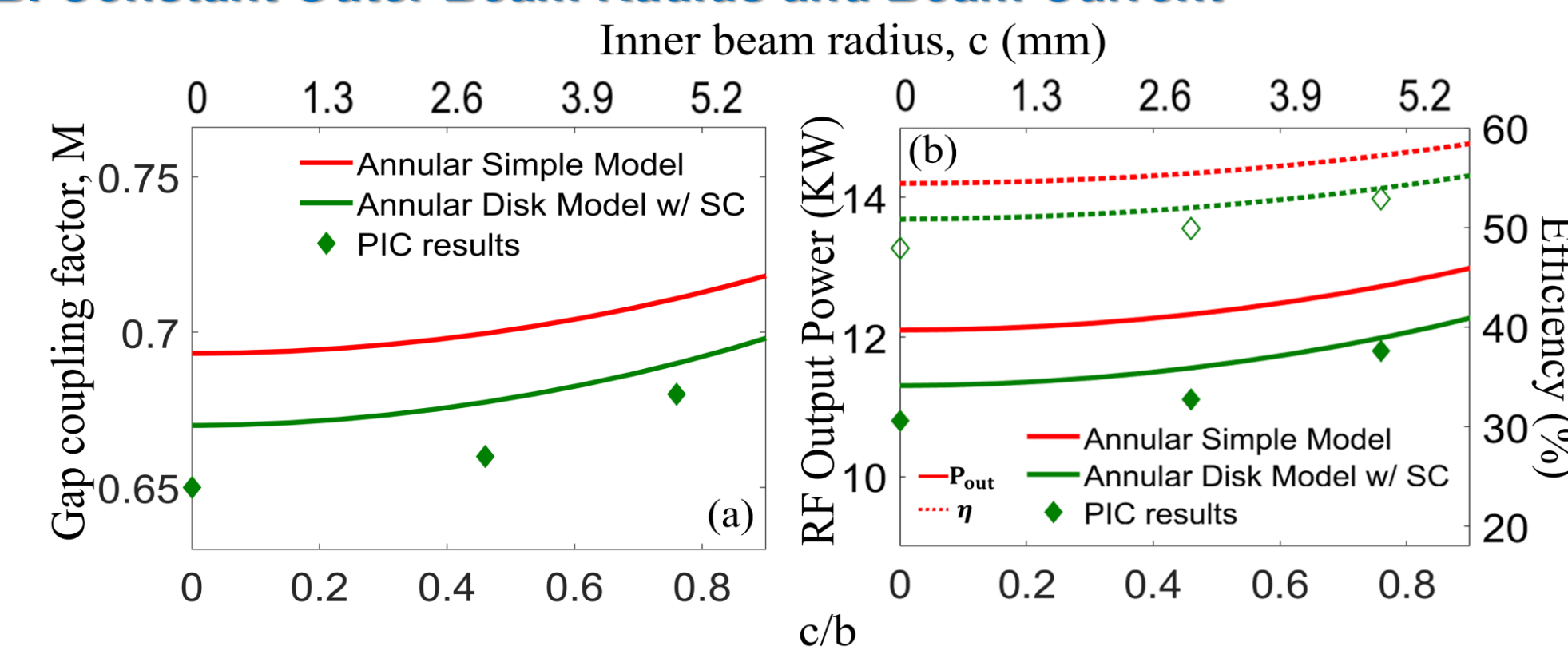


Fig. 6. Comparison of (a) M and (b) P_{RF} (solid lines) and η (dotted lines) from simple and disk model for different c and compared with PIC results (XOOPIC).

- Increasing c increases the charge density as cross-sectional area of beam is decreased due to the fixed b and total current.
- For a larger c , simple and disk models show a higher M
- Space charge effects show a reduction of up to 1.17% in M at $c = 5\text{mm}$, which is lower than solid beam.
- P_{RF} and η increase with a larger c , confirmed with PIC results (XOOPIC).

C. Electron Velocity and Kinetic Energy

- The green line (when $c/b = 0$) indicates a solid beam.
- In Fig. 7a and Fig. 8a, beam cross-sectional area is constant and b is used as 6.5mm, 7.5mm and 9.5 mm for $c/b = 0, 0.5$, and 0.7
- In Fig. 7b, and Fig. 8b, b is fixed and c varies as 0, 5 and 6.49mm
- Increasing c causes a reduction in final electron velocity, indicates that more energy is transferred from beam to the microwave field.
- Normalized $KE(= \sum KE / N_D) / KE_0$ decreases when c increases, where KE_0 and $\sum KE$ are initial and total kinetic energy.
- A reduction in KE indicates more efficient energy transfer from the electron beam to the RF fields.

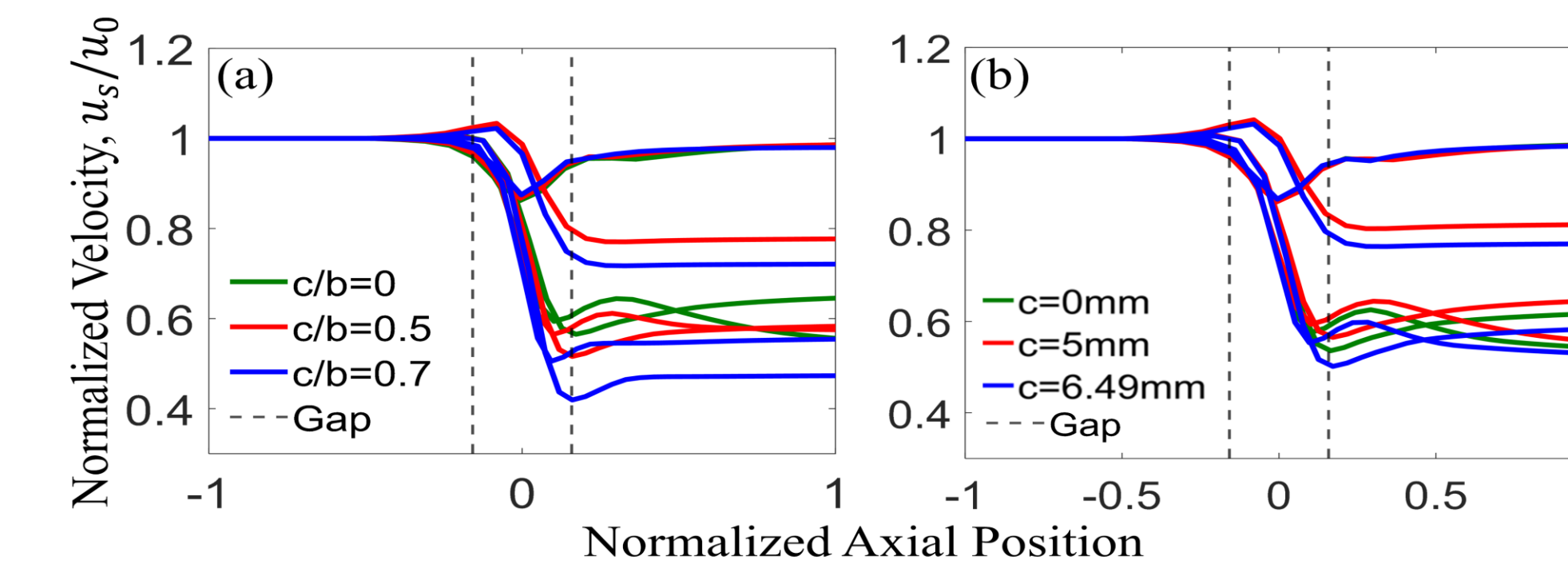


Fig. 7. Normalized velocity of disk model with space charge for different c/b of fixed beam current (a) with constant charge density and (b) with fixed b

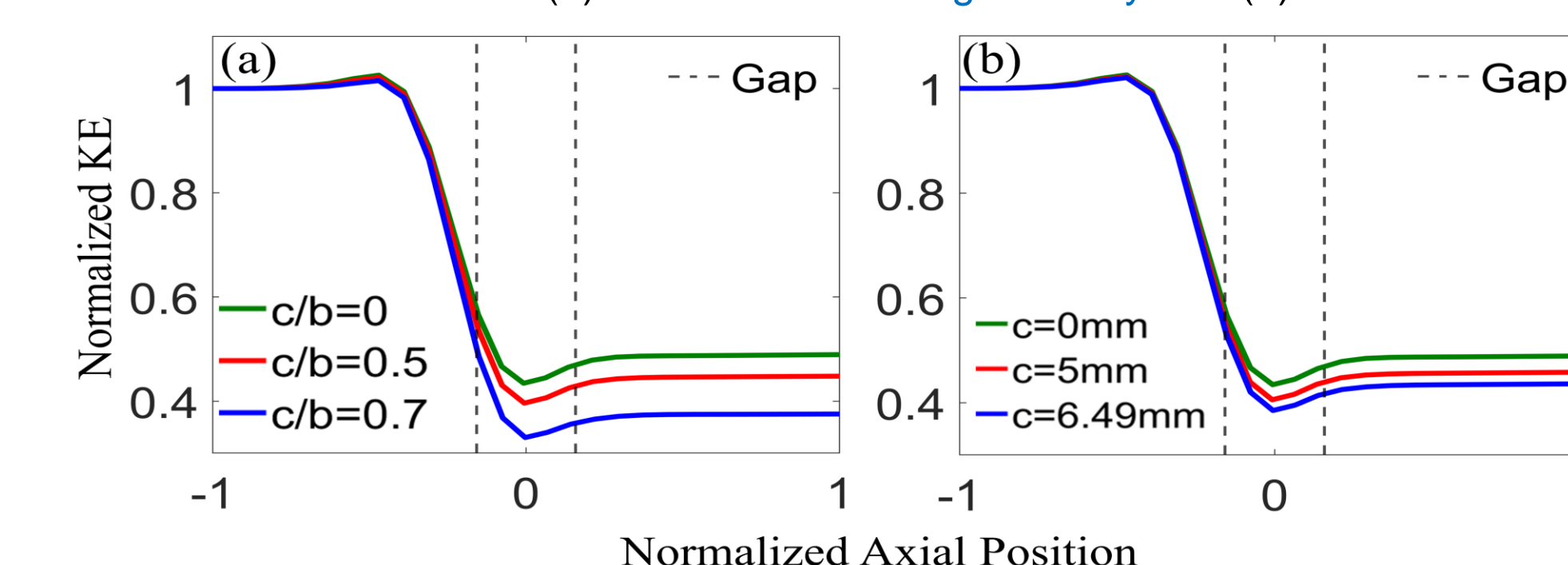


Fig. 8. Normalized KE of disk model with space charge for different c/b of fixed beam current (a) with constant charge density and (b) with fixed b

Scaling to High Frequency

- At higher frequencies, P_{RF} (solid lines) and η of the single gap-cavity device drop significantly
- At 5GHz, using $c = 5\text{mm}$ and $I_{RF} = 1.9\text{A}$, P_{RF} (η) for annular beam calculated from disk model with space charge is 16.9kW (56.9%) which are higher compared to solid beam of 11.49kW (38.3%).
- At 18GHz, we vary c while setting $V_a = 50\text{kV}$, $b = 7.2\text{mm}$, RF current $I_{RF} = 1.9\text{A}$.
- For $c = 7.15\text{mm}$, P_{RF} (η) is 20.58kW (34.6%) for disk model with space charge, which are significantly higher than solid beam ($c = 0$) of 1.93kW (3.03%).

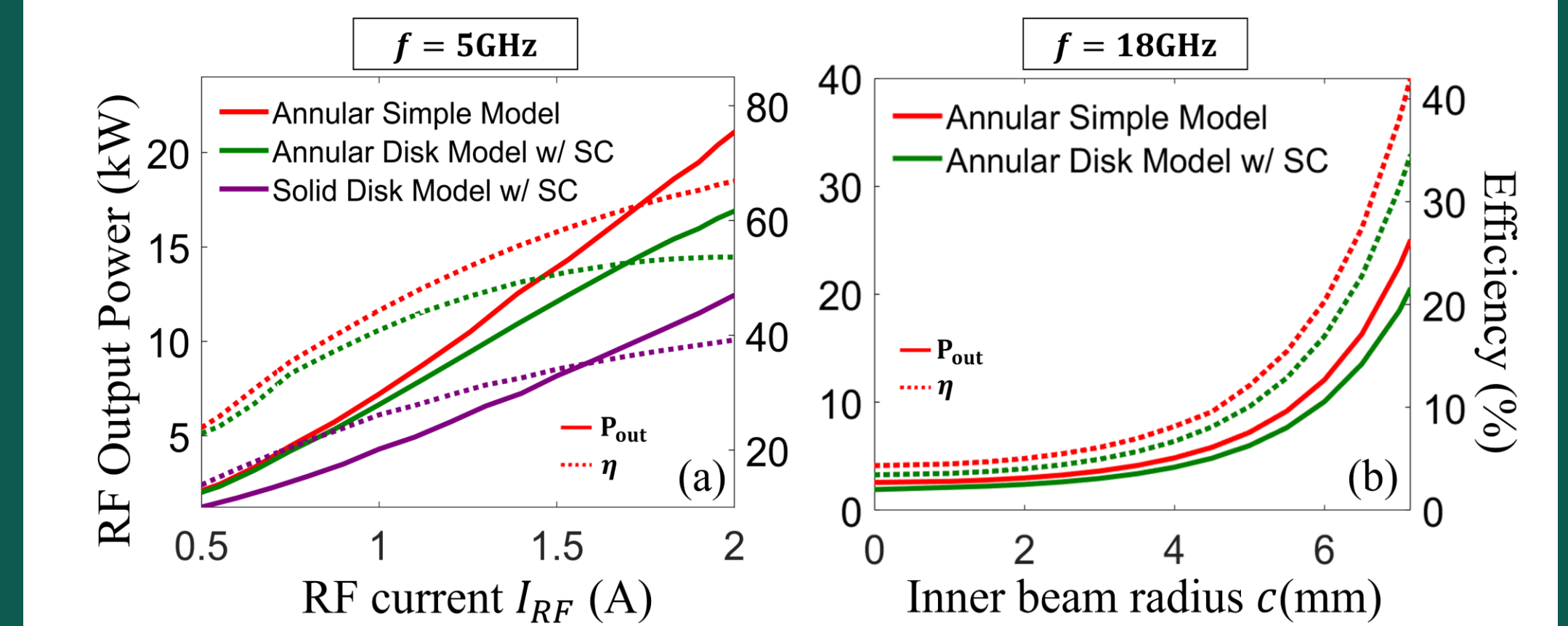


Fig. 9. Comparison of P_{RF} (solid lines) and η (dotted lines) for a single gap-cavity device (a) between annular and solid [2] beam for different RF current at $f = 5\text{GHz}$ (C-band) (b) for different c when $b = 7.2\text{mm}$ at $f = 18\text{GHz}$ (K-band).

Conclusion

- We have analysed the gap coupling factor for **annular beam-gap interaction**, using both large signal analytical model and disk model.
- We provide **parametric scaling** analyses and quantitative assessment on how increasing the **ratio of inner and outer beam radius** increases the gap coupling factor.

Future Works

- Future studies may extend the investigation to other beam profiles, including **sheet and multi-beam** configurations.
- Examine electron bunching dynamics to enable more efficient and compact high-frequency amplifiers.
- Our method may also be extended for multiple cavity devices, such as **CC-TWTs**.

References

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- [3] R. G. Carter, Microwave and RF Vacuum Electronic Power Sources, 1st ed. Cambridge University Press, 2018.

Acknowledgements

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